

新品发布

# 聚焦！SGT工艺N60V MOSFET新品，点亮清洁能源新效能

产品特点

- 1.产品采用优化的SGT工艺, 产品内阻低, 开关特性优;
- 2.产品采用TOLL、TO-263、TO-220等封装, 适用于BMS等大功率应用;
- 3.针对工控应用的各种工作状态, 优化MOS产品EAS能力, 提高产品的可靠性。

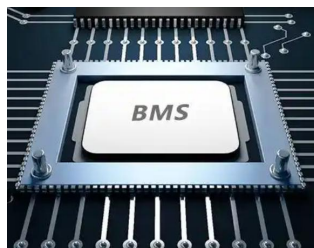
更多产品详见官网

Product Name	Package	Vds (V)	ID (A)	Vth (V) typ.	Rds10V (mohm) typ.	Rds10V (mohm) max.	Qg10V (nC) typ.	Tj (°C)	N/P
YJT2D0G06H	TOLL	60	250	3	1.62	2	81.1	-55-175	N
YJB2D3G06H	TO-263	60	220	3	1.84	2.3	79	-55-175	N

## 产品介绍

扬杰科技最新推出了一系列用于清洁能源的N60V MOSFET产品，产品采用特殊优化的SGT技术，具有较低的导通电阻Rdson和栅极电荷Qg，明显降低导通和开关损耗，同时提升了MOSFET抗冲击电流能力。

新品发布



BMS



DC-DC

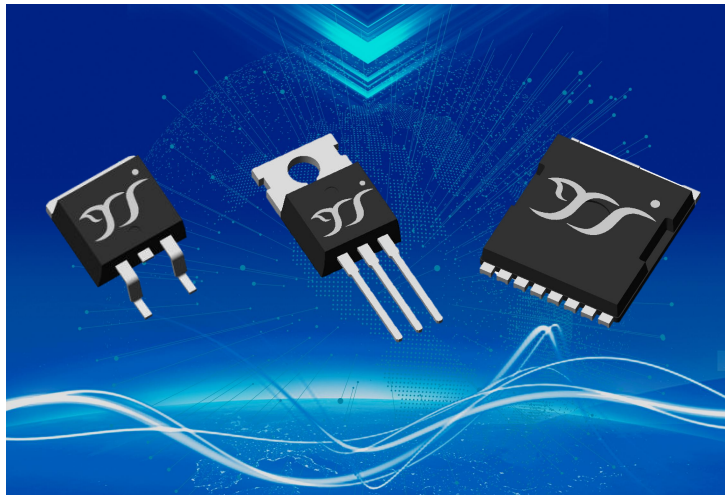


储能

典型应用

NEW  
PRODUCT

# SGT N60V MOSFET for Clean Energy Field



## Product Introduction

YangJie technology recently launched a series of N60V MOSFET products for clean energy. The products adopt specially optimized SGT technology, with low  $R_{ds(on)}$  and  $Q_g$ , significantly reducing forward voltage drop and switching losses, while enhancing the MOSFET's resistance to inrush current.

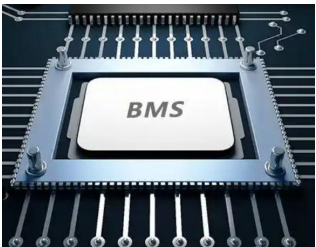
New Product Launch

## Product Features

- 1. The product utilizes optimized SGT technology, featuring low on-resistance and excellent switching performance.
- 2. It is available in packages such as TOLL, TO-263, TO-220, and is suitable for high-power applications such as BMS.
- 3. For various working states of industrial control applications, optimize the EAS capability of MOS products to enhance their reliability.

Please refer to the official website for more details

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BMS



DC-DC



Energy Storage

## Typical Applications